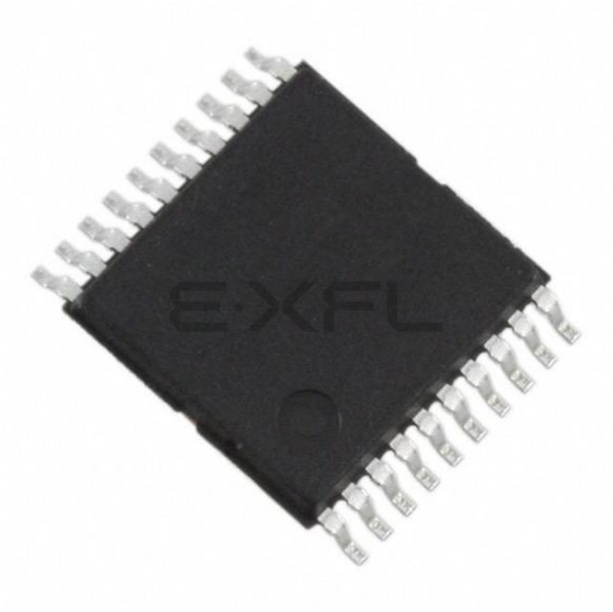
Renesas Electronics America Inc - R5F1006AASP#X0 Datasheet



What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	13
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1006aasp-x0

Table 1-1. List of Ordering Part Numbers

(11/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	A	R5F100PFAFB#V0, R5F100PGAFB#V0, R5F100PHAFB#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFB#X0, R5F100PHAFB#X0, R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0
			D	R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0, R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0 R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0, R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0, R5F100PJGFB#V0 R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0, R5F100PJGFB#X0
		Not mounted	A	R5F101PFAFB#V0, R5F101PGAFB#V0, R5F101PHAFB#V0, R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0 R5F101PFAFB#X0, R5F101PGAFB#X0, R5F101PHAFB#X0, R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
			D	R5F101PFDFB#V0, R5F101PGDFB#V0, R5F101PHDFB#V0, R5F101PJDFB#V0, R5F101PKDFB#V0, R5F101PLDFB#V0 R5F101PFDFB#X0, R5F101PGDFB#X0, R5F101PHDFB#X0, R5F101PJDFB#X0, R5F101PKDFB#X0, R5F101PLDFB#X0
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	Mounted	A	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFA#V0, R5F100PKAFA#V0, R5F100PLAFA#V0 R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0, R5F100PJAFA#X0, R5F100PKAFA#X0, R5F100PLAFA#X0
			D	R5F100PFDFA#V0, R5F100PGDFA#V0, R5F100PHDFA#V0, R5F100PJDFA#V0, R5F100PKDFA#V0, R5F100PLDFA#V0 R5F100PFDFA#X0, R5F100PGDFA#X0, R5F100PHDFA#X0, R5F100PJDFA#X0, R5F100PKDFA#X0, R5F100PLDFA#X0
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0, R5F100PJGFA#V0 R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0, R5F100PJGFA#X0
		Not mounted	A	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0, R5F101PJAFA#V0, R5F101PKAFA#V0, R5F101PLAFA#V0 R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0, R5F101PJAFA#X0, R5F101PKAFA#X0, R5F101PLAFA#X0
			D	R5F101PFDFA#V0, R5F101PGDFA#V0, R5F101PHDFA#V0, R5F101PJDFA#V0, R5F101PKDFA#V0, R5F101PLDFA#V0 R5F101PFDFA#X0, R5F101PGDFA#X0, R5F101PHDFA#X0, R5F101PJDFA#X0, R5F101PKDFA#X0, R5F101PLDFA#X0

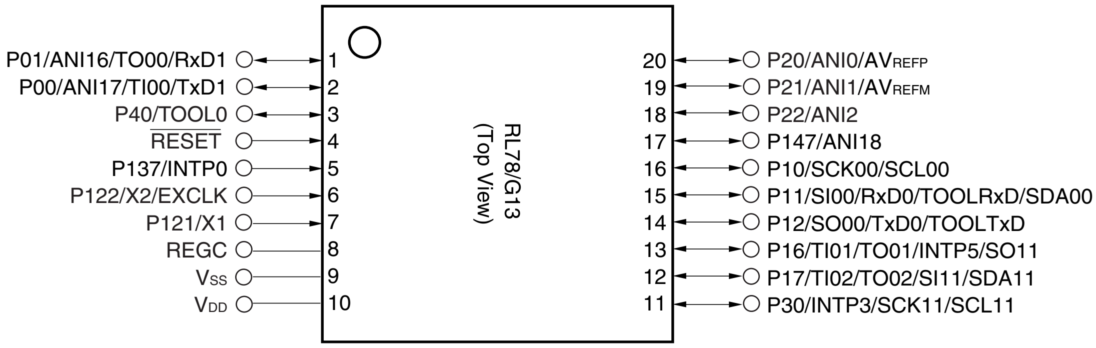
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

- 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

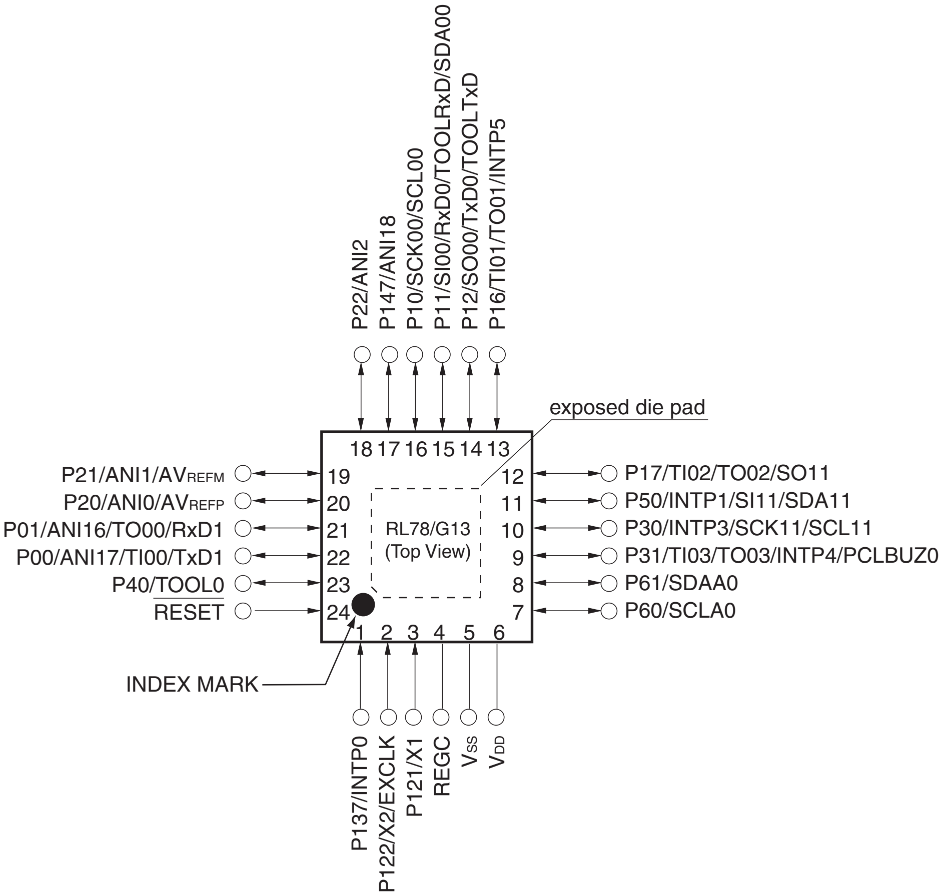


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remark For pin identification, see **1.4 Pin Identification**.

1.3.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



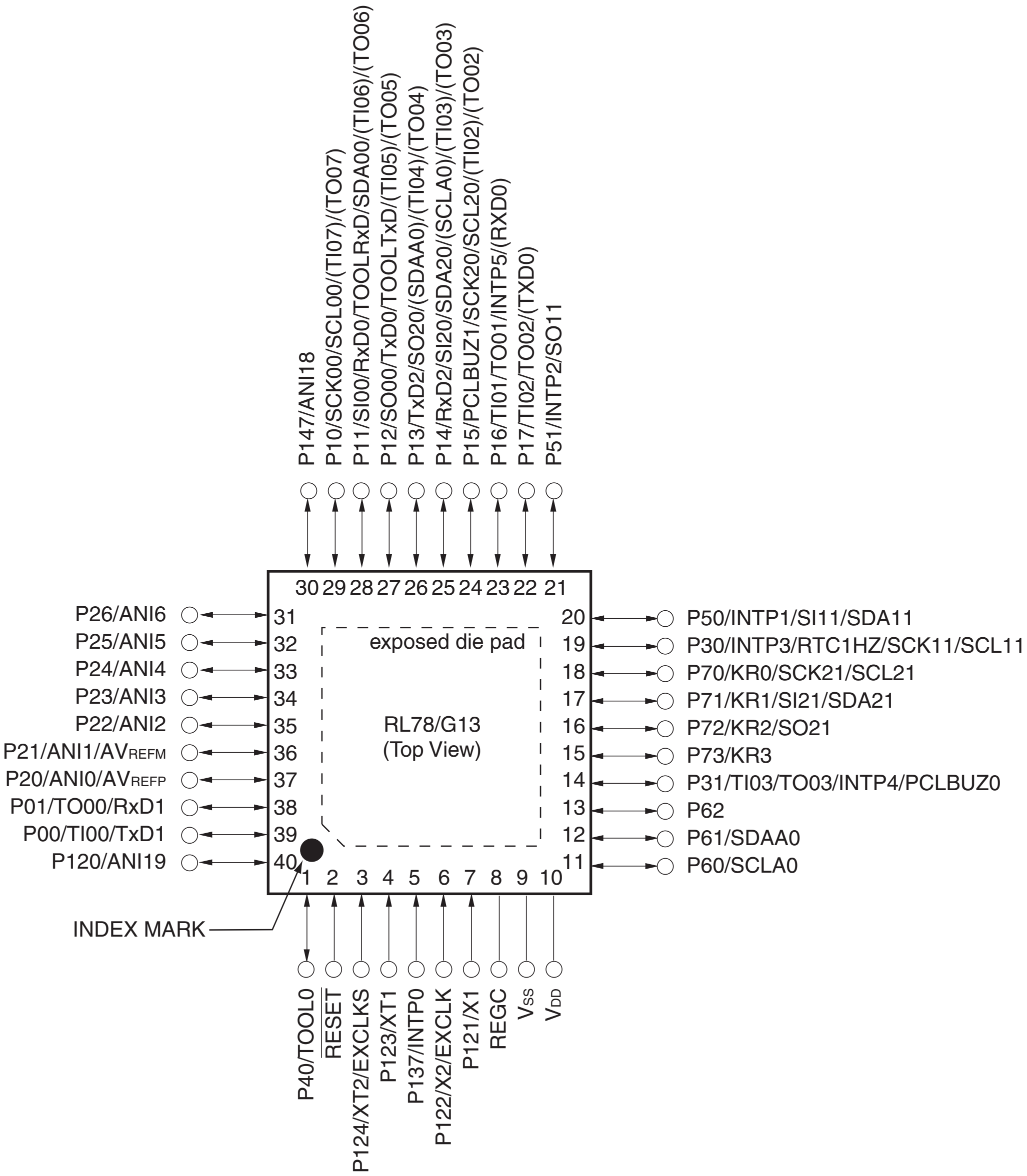
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. It is recommended to connect an exposed die pad to V_{SS}.

1.3.7 40-pin products

- 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

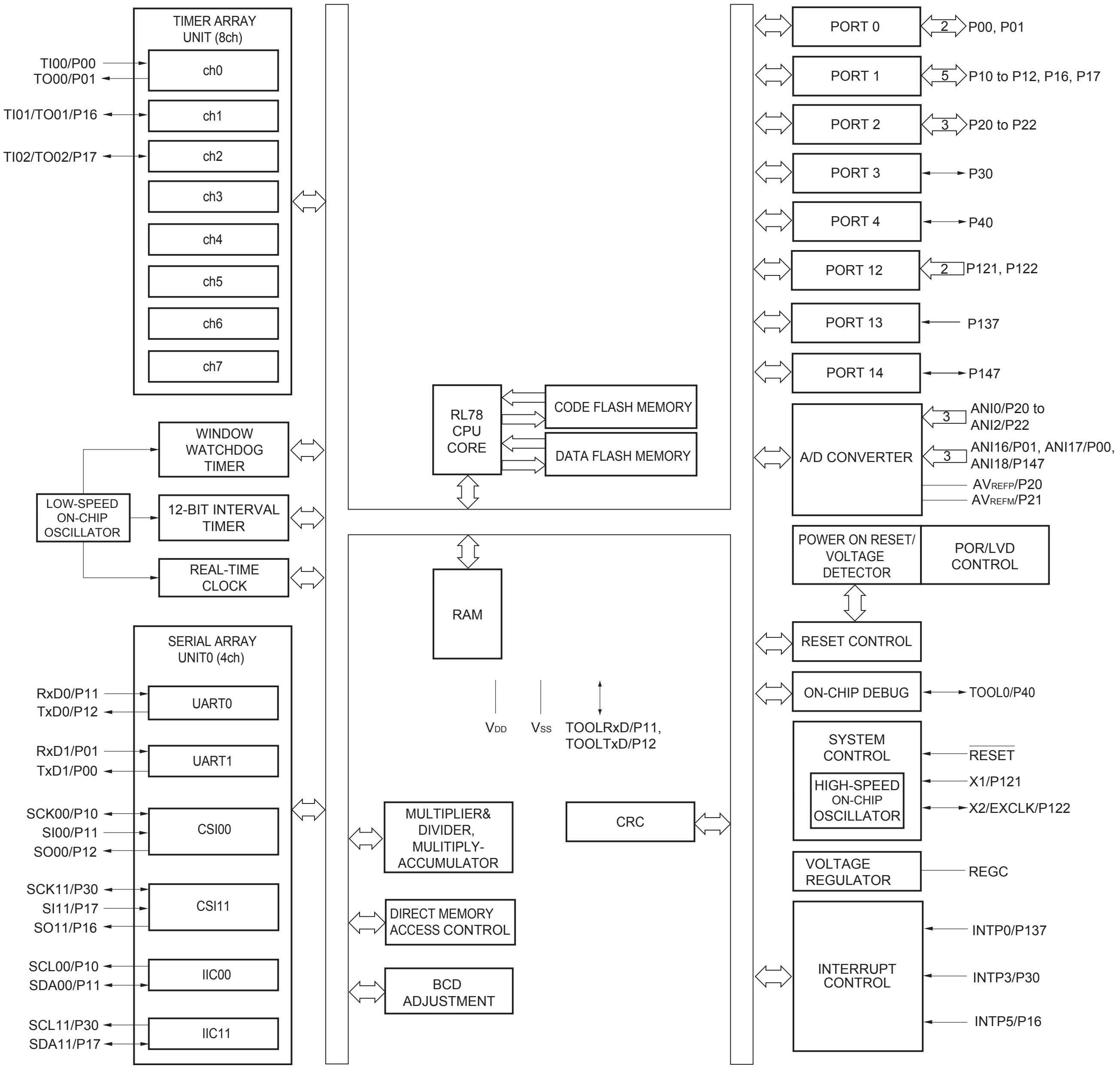
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

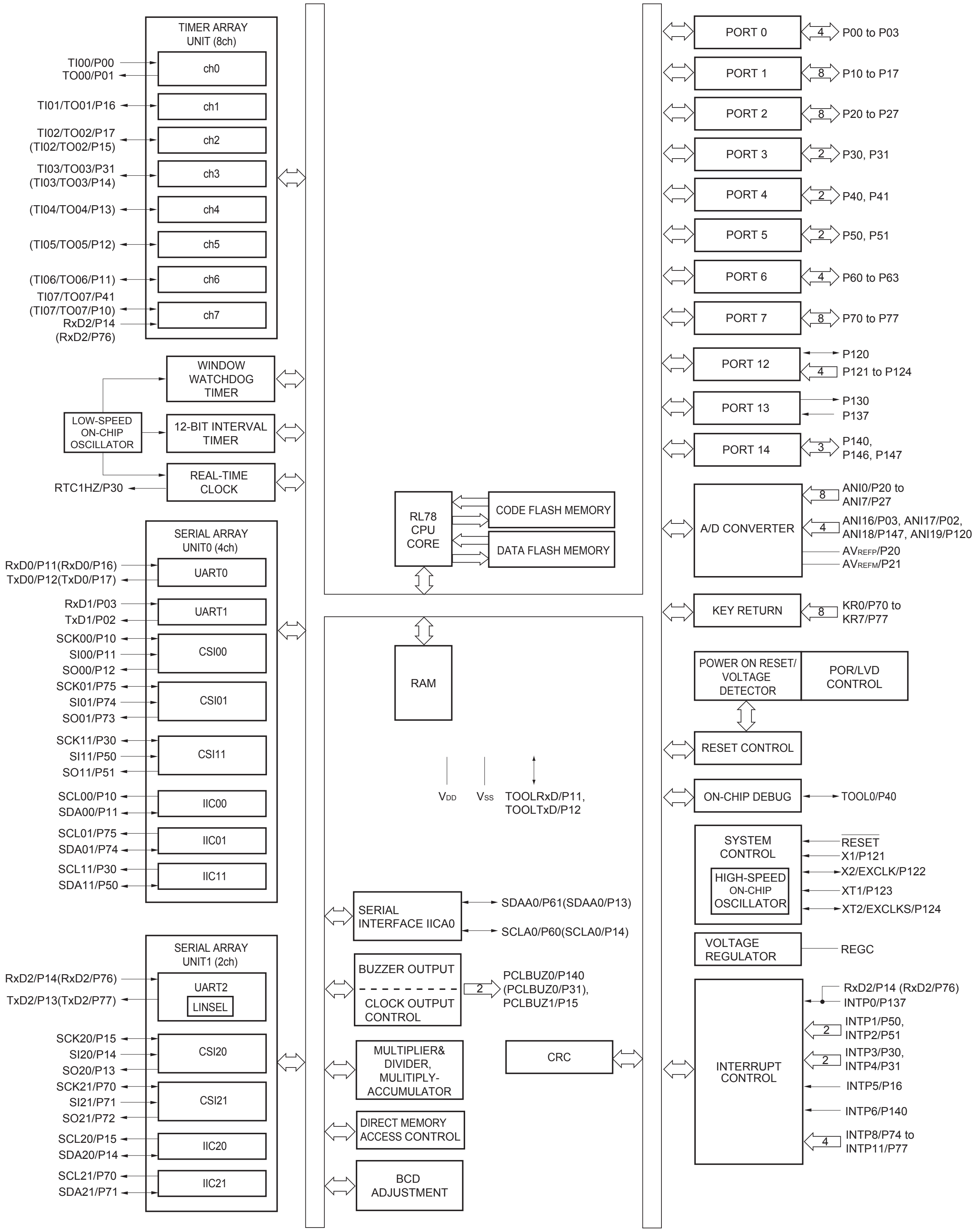
3. It is recommended to connect an exposed die pad to V_{SS}.

1.5 Block Diagram

1.5.1 20-pin products



1.5.10 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash memory (KB)		16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128	
Data flash memory (KB)		4	–	4	–	4	–	4 to 8	–	4 to 8	–	4 to 8	–
RAM (KB)		2 to 4[Note1]		2 to 4[Note1]		2 to 4[Note1]		2 to 12[Note1]		2 to 12[Note1]		2 to 12[Note1]	
Address space		1 MB											
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)											
Subsystem clock		–											
Low-speed on-chip oscillator		15 kHz (TYP.)											
General-purpose registers		(8-bit register × 8) × 4 banks											
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f_{IH} = 32 MHz operation)											
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)											
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.											
I/O port	Total	16		20		21		26		28		32	
	CMOS I/O	13 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)		21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		22 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)		26 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)	
	CMOS input	3		3		3		3		3		3	
	CMOS output	–		–		1		–		–		–	
	N-ch O.D. I/O (withstand voltage: 6 V)	–		2		2		2		3		3	
Timer	16-bit timer	8 channels											
	Watchdog timer	1 channel											
	Real-time clock (RTC)	1 channel [Note 2]											
	12-bit interval timer (IT)	1 channel											
	Timer output	3 channels (PWM outputs: 2 [Note 3])		4 channels (PWM outputs: 3 [Note 3])				4 channels (PWM outputs: 3 [Note 3]), 8 channels (PWM outputs: 7 [Note 3]) [Note 4]					
	RTC output	–											

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H
R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		40-pin		44-pin		48-pin		52-pin		64-pin	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Code flash memory (KB)		16 to 192		16 to 512		16 to 512		32 to 512		32 to 512	
Data flash memory (KB)		4 to 8	–	4 to 8	–	4 to 8	–	4 to 8	–	4 to 8	–
RAM (KB)		2 to 16[Note1]		2 to 32[Note1]		2 to 32[Note1]		2 to 32[Note1]		2 to 32[Note1]	
Address space		1 MB									
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)									
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)									
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz									
Low-speed on-chip oscillator		15 kHz (TYP.)									
General-purpose registers		(8-bit register × 8) × 4 banks									
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f_{IH} = 32 MHz operation)									
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)									
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)									
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.									
I/O port	Total	36		40		44		48		58	
	CMOS I/O	28 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)		31 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)		34 (N-ch O.D. I/O [V_{DD} withstand voltage]: 11)		38 (N-ch O.D. I/O [V_{DD} withstand voltage]: 13)		48 (N-ch O.D. I/O [V_{DD} withstand voltage]: 15)	
	CMOS input	5		5		5		5		5	
	CMOS output	–		–		1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	3		4		4		4		4	
Timer	16-bit timer	8 channels									
	Watchdog timer	1 channel									
	Real-time clock (RTC)	1 channel									
	12-bit interval timer (IT)	1 channel									
	Timer output	4 channels (PWM outputs: 3[Note 2]), 8 channels (PWM outputs: 7[Note 2])[Note 3]		5 channels (PWM outputs: 4[Note 2]), 8 channels (PWM outputs: 7[Note 2])[Note 3]						8 channels (PWM outputs: 7[Note 2])	
	RTC output	1 channel • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)									

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H
R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H
R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H
R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	−40	mA
		Total of all pins −170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	−70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	−100	mA
	I_{OH2}	Per pin	P20 to P27, P150 to P156	−0.5	mA
		Total of all pins		−2	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	I_{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A	In normal operation mode		−40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			−65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = –10.0 mA	EV_{DD0} – 1.5			V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = –3.0 mA	EV_{DD0} – 0.7			V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = –2.0 mA	EV_{DD0} – 0.6			V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = –1.5 mA	EV_{DD0} – 0.5			V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OH1} = –1.0 mA	EV_{DD0} – 0.5			V
	V_{OH2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = –100 μA	V_{DD} – 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD0} < 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD2} [Note 2]	HALT mode	HS (high-speed main) mode [Note 7]	f_{IH} = 32 MHz [Note 4]	V_{DD} = 5.0 V		0.62	1.86	mA
					V_{DD} = 3.0 V		0.62	1.86	mA
				f_{IH} = 24 MHz [Note 4]	V_{DD} = 5.0 V		0.50	1.45	mA
					V_{DD} = 3.0 V		0.50	1.45	mA
				f_{IH} = 16 MHz [Note 4]	V_{DD} = 5.0 V		0.44	1.11	mA
					V_{DD} = 3.0 V		0.44	1.11	mA
			LS (low-speed main) mode [Note 7]	f_{IH} = 8 MHz [Note 4]	V_{DD} = 3.0 V		290	620	μA
					V_{DD} = 2.0 V		290	620	μA
			LV (low-voltage main) mode [Note 7]	f_{IH} = 4 MHz [Note 4]	V_{DD} = 3.0 V		440	680	μA
					V_{DD} = 2.0 V		440	680	μA
			HS (high-speed main) mode [Note 7]	f_{MX} = 20 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 20 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.31	1.08	mA
					Resonator connection		0.48	1.28	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
				f_{MX} = 10 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.21	0.63	mA
					Resonator connection		0.28	0.71	mA
			LS (low-speed main) mode [Note 7]	f_{MX} = 8 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
				f_{MX} = 8 MHz [Note 3], V_{DD} = 2.0 V	Square wave input		110	360	μA
					Resonator connection		160	420	μA
			Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 5] T_A = –40°C	Square wave input		0.28	0.61	μA
					Resonator connection		0.47	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +25°C	Square wave input		0.34	0.61	μA
					Resonator connection		0.53	0.80	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +50°C	Square wave input		0.41	2.30	μA
					Resonator connection		0.60	2.49	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +70°C	Square wave input		0.64	4.03	μA
					Resonator connection		0.83	4.22	μA
				f_{SUB} = 32.768 kHz [Note 5] T_A = +85°C	Square wave input		1.09	8.04	μA
					Resonator connection		1.28	8.23	μA
	I_{DD3} [Note 6]	STOP mode [Note 8]	T_A = –40°C				0.19	0.52	μA
			T_A = +25°C				0.25	0.52	μA
			T_A = +50°C				0.32	2.21	μA
			T_A = +70°C				0.55	3.94	μA
			T_A = +85°C				1.00	7.95	μA

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current . However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 32 MHz
	$2.4\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 16 MHz
LS (low-speed main) mode:	$1.8\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 8 MHz
LV (low-voltage main) mode:	$1.6\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) [Note 1]	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V [Note 2], C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) [Note 1]	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V [Note 2], C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output [Note 1]	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V [Note 2], C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

Notes **1.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with EV_{DD0} ≥ V_b.

Caution **Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2)

($T_A = -40$ to +85°C, $1.8\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	$1/f_{MCK} + 135^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		kHz
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	$1/f_{MCK} + 135^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		kHz
		$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 100\ pF$, $R_b = 2.8\ k\Omega$	$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		kHz
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 100\ pF$, $R_b = 2.7\ k\Omega$	$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		kHz
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V^{\text{Note 2}}$, $C_b = 100\ pF$, $R_b = 5.5\ k\Omega$	$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		$1/f_{MCK} + 190^{\text{Note 3}}$		kHz
Data hold time (transmission)	$t_{HD:DAT}$	$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	0	305	0	305	0	305	ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	0	305	0	305	0	305	ns
		$4.0\ V \le EV_{DD0} \le 5.5\ V$, $2.7\ V \le V_b \le 4.0\ V$, $C_b = 100\ pF$, $R_b = 2.8\ k\Omega$	0	355	0	355	0	355	ns
		$2.7\ V \le EV_{DD0} < 4.0\ V$, $2.3\ V \le V_b \le 2.7\ V$, $C_b = 100\ pF$, $R_b = 2.7\ k\Omega$	0	355	0	355	0	355	ns
		$1.8\ V \le EV_{DD0} < 3.3\ V$, $1.6\ V \le V_b \le 2.0\ V^{\text{Note 2}}$, $C_b = 100\ pF$, $R_b = 5.5\ k\Omega$	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Use it with $EV_{DD0} \ge V_b$.

3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

2.5.2 Serial interface IICA

(1) I^2C standard mode

(T_A = −40 to +85°C, 1.6 V ≤ $EV_{DD0} = EV_{DD1} \le V_{DD} \le$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: $f_{CLK} \ge$ 1 MHz	2.7 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		0	100	0	100	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.7		4.7		μs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.0		4.0		μs
Hold time when SCLA0 = "L"	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.7		4.7		μs
Hold time when SCLA0 = "H"	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.0		4.0		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		250		250		250		ns
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		250		250		250		ns
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		250		250		250		ns
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		250		250		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		0	3.45	0	3.45	μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.0		4.0		μs
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.7		4.7		μs

(**Notes**, **Caution** and **Remark** are listed on the next page.)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD}, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} [Note 3], Reference voltage (–) = AV_{REFM} = 0 V [Note 4], HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error [Notes 1, 2]	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error [Note 1]	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error [Note 1]	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} [Note 3]	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

2.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

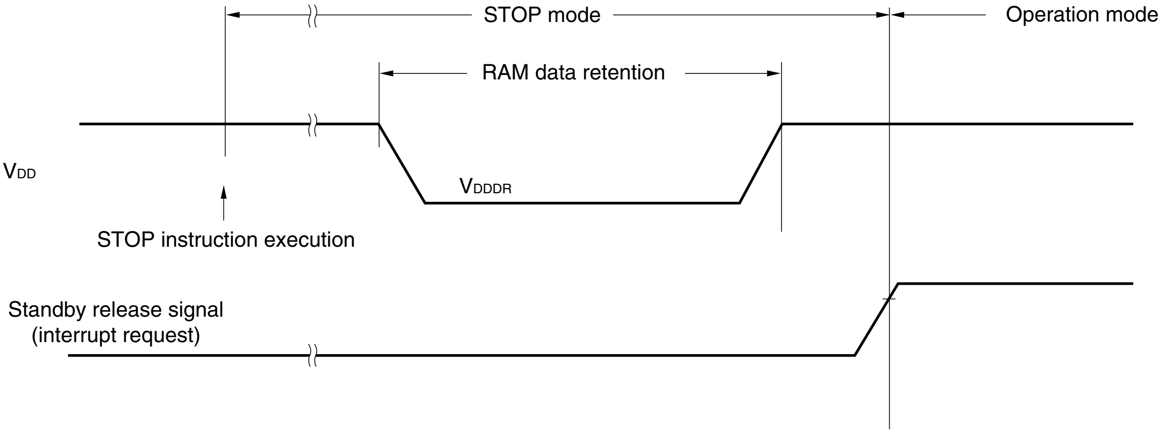
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46[Note]		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



(4) During communication at same potential (simplified I^{2}C mode)

(T_A = −40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note1	kHz
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		100 Note1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 220 Note2		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

Notes **1.** The value must also be equal to or less than f_{MCK}/4.

2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

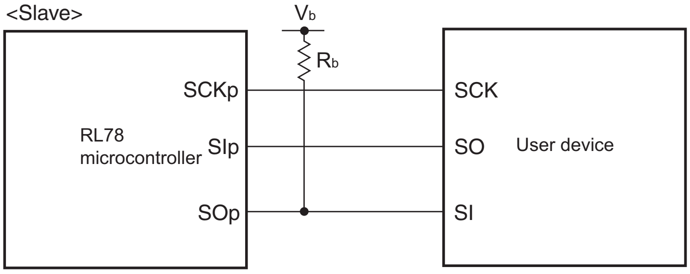
2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

3.8 Flash Memory Programming Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	2.4 V ≤ V_{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1,2,3	C_{erwr}	Retained for 20 years T_A = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1,2,3		Retained for 1 years T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C Note 4	100,000			
		Retained for 20 years T_A = 85°C Note 4	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library.

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps